

Electronic and Optoelectronic Physics in the van der Waals Heterojunctions

Philip Kim

Harvard University

Recent advance of van der Waals (vdW) materials and their heterostructures provide a new opportunity to realize atomically sharp interfaces in the ultimate quantum limit. By assembling atomic layers of vdW materials, such as hexa boronitride, transition metal chalcogenide and graphene, we can construct novel quantum structures. Unlike conventional semiconductor heterostructures, charge transport of the devices are found to critically depend on the interlayer charge transport, electron-hole recombination process mediated by tunneling across the interface. We demonstrate the enhanced electronic optoelectronic performances in the vdW heterostructures, tuned by applied gate voltages, suggesting that these a few atom thick interfaces may provide a fundamental platform to realize novel physical phenomena, such as hydrodynamic charge flows, cross-Andreev reflection across the quantum Hall edges states, and interlayer exciton formation and manipulations.